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(71) Applicant *(for all designated States except US)*: LAM RESEARCH CORPORATION [US/US]; 4650 Cushing Parkway, Fremont, CA 94538-4670 (US). SEE PF23

(72) Inventors; and

(75) Inventors/Applicants *(for US only)*: HOLLAND, John, P. [US/US]; 617 Enright Avenue, Santa Clara, CA 95050 (US). DEMOS, Alex, T. [US/US]; 1762 Bay Street, San Francisco, CA 94123 (US).

(74) Agents: BEDI, Harmohinder, S. et al.; Hickman Beyer & Weaver, P.O. Box 61059, Palo Alto, CA 94306 (US).

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(54) Title: DRY ETCHING OF TRANSPARENT ELECTRODES IN A LOW PRESSURE PLASMA REACTOR

(57) Abstract

A method for dry etching an indium tin oxide (ITO) layer disposed above a substrate in a low pressure plasma reactor is disclosed. The method includes a step of placing a substrate having the ITO layer into the low pressure plasma reactor, a step of introducing an etchant gas into the low pressure plasma reactor, a step of striking a plasma from the etchant gas in the low pressure plasma reactor, and a step of etching the ITO layer with the plasma.

